

DATASHEET

Side Face Silicon Phototransistor PT5529B/L2/H2-F354



Features

- Fast response time
- · High photo sensitivity
- Pb free
- This product itself will remain within RoHS compliant version.
- Compliance with EU REACH
- Compliance Halogen Free .(Br <900 ppm ,Cl <900 ppm , Br+Cl < 1500 ppm)

Description

- PT5529B/L2/H2-F354 is a high speed and high sensitive dual phototransistor molded in a black plastic package with plat side view.
- The device is spectrally matched with IR emitters.

Applications

- Mouse
- Optoelectronic Switch
- Photo Interrupter



Device Selection Guide

LED Part No	Chip Materials	Lens Color	
PT5529B/L2/H2-F354	Silicon	Black	

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Unit	
Collector-Emitter Voltage	$V_{\sf CEO}$	30	V	
Emitter-Collector-Voltage	V _{ECO} 5		V	
Collector Current	lc	20	mA	
Operating Temperature	Topr	-40 ~ +85°C	$^{\circ}\mathbb{C}$	
Storage Temperature	Tstg	-40 ~ +85°C	${\mathbb C}$	
Lead Soldering Temperature(*1)	Tsol	260	$^{\circ}\mathbb{C}$	
Power Dissipation at (or below) 25°C Free Air Temperature	P _D	75	mW	
Notes: *1:Soldering time≦5 seconds	RL			



Electro-Optical Characteristics (Ta=25°C)

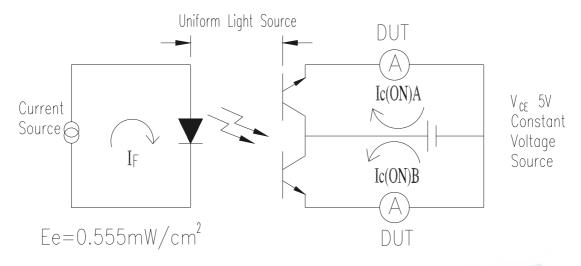
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Collector – Emitter Breakdown Voltage	BV _{CEO}	I _C =100μA Ee=0mW/cm ²	30			V
Emitter-Collector Breakdown Voltage	BV _{ECO}	I _E =100μA Ee=0mW/cm ²	5			V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =2mA Ee=1mW/cm ²			0.4	V
Rise Time	t _r	V _{CE} =5V I _C =1mA		15		μS
Fall Time	t _f	$R_L = 1000\Omega$		15		
Collector Dark Current	I _{CEO}	Ee=0mW/cm ² V _{CE} =20V			100	nA
On State Collector Current	I _{C(on)}	V _{CE} =5V, Ee=0.555mW/cm ²	129		1085	μΑ
Wavelength of Peak Sensitivity	λр			940		nm
Rang of Spectral Bandwidth	λ _{0.5}		760		1100	nm



Test Method For On State Collector Current:

$$\label{eq:condition} \begin{split} & Condition: Ee=0.555mW/cm^2 \ , \ V_{\text{CE}}=5V \\ & Test \ Item: Collector \ Current \ [I_{C(on)}] \end{split}$$

Unit: µA

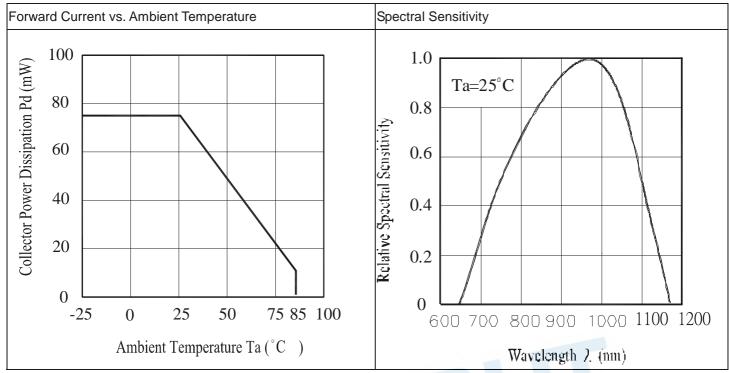


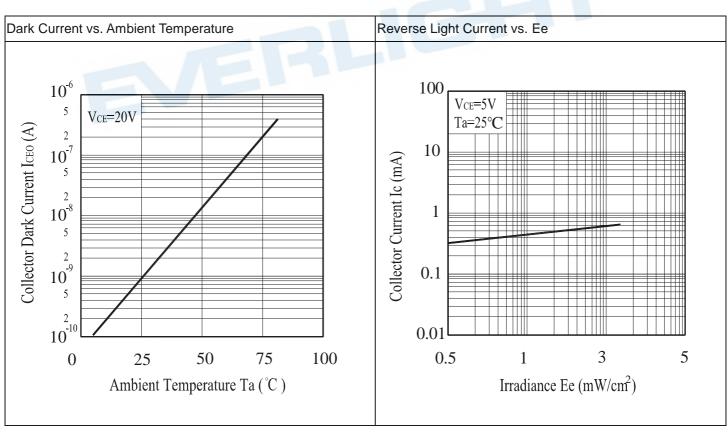
To Distinguish Intensity: Condition:V_{CE}:5V Ee:0.555mW/cm² Ranks

Ranks	Symbol	Min	Тур	Max	Unit	Text Condition
A1	IC(on)	129		226	μΑ	Ee=0.555mW/cm ² V _{GE} =5V
A2	IC(on)	195		306	μΑ	Ee=0.555mW/cm ² Va=5V
A3	IC(on)	262		380	μΑ	Ee=0,555mW/cm ² Va=5V
A4	IC(on)	330		461	μΑ	Ee=0.555mW/cm ² Va=5V
A5	IC(on)	398		544	μΑ	Ee=0.555mW/cm ² V _{GE} =5V
A6	IC(on)	468		625	μΑ	Ee=0.555mW/cm ² Va=5V
A7	IC(on)	536		703	μΑ	Ee=0.555mW/cm ² Va=5V
A8	IC(on)	604		785	μΑ	Ee=0.555mW/cm ² Va=5V
A9	IC(on)	673		862	μΑ	Ee=0.555mW/cm ² Va=5V
A10	IC(on)	742		944	μΑ	Ee=0.555mW/cm ² Va=5V
A11	IC(on)	812		1018	μΑ	Ee=0.555mW/cm ² Va=5V
A12	IC(on)	882		1085	μΑ	Ee=0.555mW/cm ² V _E =5V



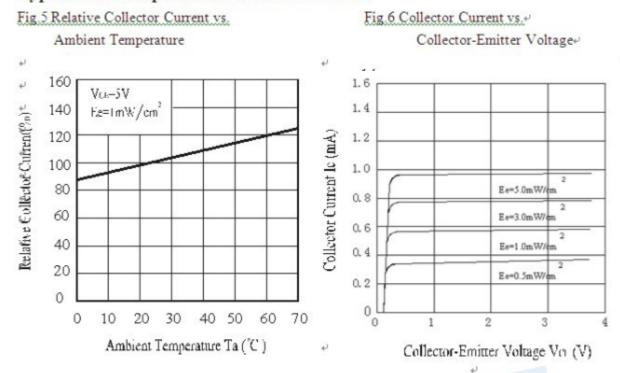
Typical Electro-Optical Characteristics Curves







Typical Electro-Optical Characteristics Curves-



Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

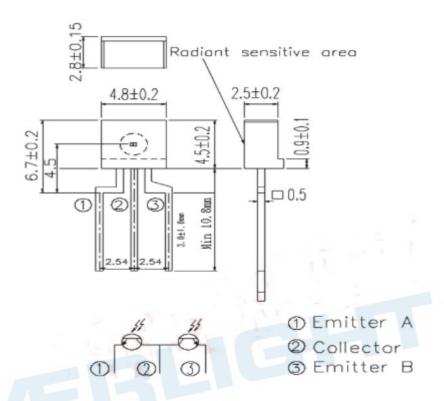
Confidence level: 90%

LTPD: 10%

NO.	Itemø	Test Conditions	Test Hours/↓ Cycles↓	Sample⊬ Sizes⊬	Failure ↓ Judgement↓ Criteria↓	Ac/Re∂
1₽	Solder Heat≎	TEMP. : 260°C₽	10secs₽	22pcs₽		0/1₽
20	Temperature Cycle∂	H:+100°C 15mins# L:-40°C 15mins#	300Cycles₽	22pcs+	F IC(ON) ≤ L×0.8+1 F L: the initial test value+1 F	0/1₽
3€	Thermal Shock∘	H:+100°C 5mins-10secs- L:-10°C 5mins-1	_	22pcs₽		0/1∻
40	High Temperature↓ Storage↓	TEMP. : +100°C₀	1000hrs₽	22pcs₽		0/1₽
50	Low Temperature≠ Storage≠	TEMP. : -40°C₽	1000hrs₽	22pcs₽		0/1₽
60	DC Operating Life	V _{CE} =5V ₄	1000hrs≠	22pcs₽		0/143
7₽	High Temperature/↓ High Humidity¢	85℃ / 85% R.H <i>e</i>	1000hrs₽	22pcs₽		0/1₽



Package Dimension



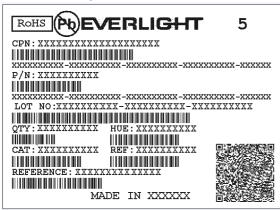
Note: Tolerances unless dimensions ±0.25mm



Packing Quantity Specification

- 1. 1000PCS/1Bag,10Bag/1Box
- 2. 10Boxes/1Carton

Label Form Specification



- CPN: Customer's Product Number
- P/N: Product Number
- · QTY: Packing Quantity
- CAT: Luminous Intensity RankHUE: Dom. Wavelength Rank
- REF: Forward Voltage Rank
- · LOT No: Lot Number
- · X: Month
- · Reference: Identify Label Number

Notes

Lead Forming

- During lead formation, the leads should be bent at a point at least 3mm from the base of the epoxy bulb.
- Lead forming should be done before soldering.
- Avoid stressing the Phototransistor package during leads forming. The stress to the base may damage the Phototransistor's characteristics or it may break the Phototransistor.
- Cut the Phototransistor lead frames at room temperature. Cutting the lead frames at high temperatures may cause failure of the Phototransistor.
- When mounting the Phototransistor onto a PCB, the PCB holes must be aligned exactly with the lead position of the Phototransistor. If the Phototransistor are mounted with stress at the leads, it causes deterioration of the epoxy resin and this will degrade the Phototransistor.

2. Storage

- The Phototransistor should be stored at 30°C or less and 70%RH or less after being shipped from Everlight and the storage life limits are 3 months. If the Phototransistor are stored for 3 months or more, they can be stored for a year in a sea Phototransistor container with a nitrogen atmosphere and moisture absorbent material.
- Please avoid rapid transitions in ambient temperature, especially, in high humidity environments where condensation can occur.

Soldering

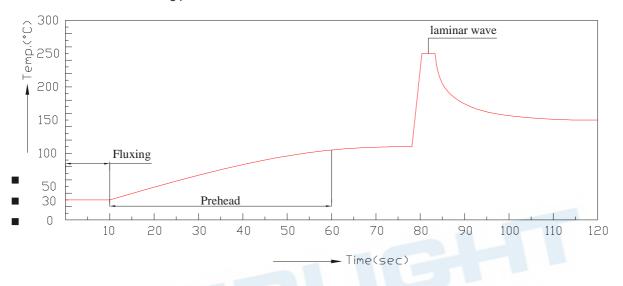
Careful attention should be paid during soldering. When soldering, leave more then 3mm from solder joint to epoxy bulb, and soldering beyond the base of the tie bar is recommended.



Recommended soldering conditions:

Hand Soldering		DIP Soldering			
Temp. at tip of iron 300°C Max. (30W Max.)		Preheat temp.	100°C Max. (60 sec Max.)		
Soldering time	3 sec Max.	Bath temp. & time	260 Max., 5 sec Max		
Distance	3mm Min.(From solder joint to epoxy bulb)	Distance	3mm Min. (From solder joint to epoxy bulb)		

Recommended soldering profile



- Avoiding applying any stress to the lead frame while the Phototransistor are at high temperature particularly when soldering.
- Dip and hand soldering should not be done more than one time
- After soldering the Phototransistor, the epoxy bulb should be protected from mechanical shock or vibration until the Phototransistor return to room temperature.
- A rapid-rate process is not recommended for cooling the Phototransistor down from the peak temperature.

 Although the recommended soldering conditions are specified in the above table, dip or hand soldering at the lowest possible temperature is desirable for the Phototransistor.
- Wave soldering parameter must be set and maintain according to recommended temperature and dwell time in the solder wave.

4. Cleaning

- When necessary, cleaning should occur only with isopropyl alcohol at room temperature for a duration of no more than one minute. Dry at room temperature before use.
- Do not clean the Phototransistor by the ultrasonic. When it is absolutely necessary, the influence of ultrasonic cleaning on the Phototransistor depends on factors such as ultrasonic power and the assembPhototransistor condition. Ultrasonic cleaning shall be pre-qualified to ensure this will not cause damage to the PHOTOTRANSISTOR

5. Heat Management

Heat management of Phototransistor must be taken into consideration during the design stage of PHOTOTRANSISTOR application. The current should be de-rated appropriately by referring to the de-rating curve found in each product



specification.

- The temperature surrounding the PHOTOTRANSISTOR in the application should be controlPhototransistor. Please refer to the data sheet de-rating curve.
- 6. ESD (Electrostatic Discharge)
 - Electrostatic discharge (ESD) or surge current (EOS) can damage Phototransistor.
 - An ESD wrist strap, ESD shoe strap or antistatic gloves must be worn whenever handling Phototransistor.
 - All devices, equipment and machinery must be properly grounded.
 - Use ion blower to neutralize the static charge which might have built up on surface of the Phototransistor plastic lens as a result of friction between Phototransistor during storage and handing.

DISCLAIMER

- 1. EVERLIGHT reserves the right(s) on the adjustment of product material mix for the specification.
- 2. The product meets EVERLIGHT published specification for a period of twelve (12) months from date of shipment.
- 3. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
- 4. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from the use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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